

Features

- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

Applications

- Normally-on switches
- Solid state relays
- Converters
- Constant current sources
- Power supply circuits
- Telecom

General Description

The Supertex DN3145 is a depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV _{DSX} /BV _{DGX}	R _{DS(ON)}	I _{DSS}		cieen Initiaria		
Device	TO-243AA (SOT-89)	(V)	(max) (Ω)	(min) (mA)	(\mathbb{N})			
DN3145	DN3145N8-G	450	60	120		99 (Pb)-4		

-G indicates package is RoHS compliant ('Green')

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSX}
Drain-to-gate voltage	BV _{DGX}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

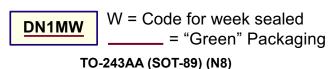
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6mm from case for 10 seconds.

Pin Configuration



Product Marking



Thermal Characteristics

Package	Ι _D (continuous) [†] (mA)	Ι _D (pulsed) (mA)	Power Dissipation @T _A = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	l _{DR} † (mA)	l _{DRM} (mA)
TO-243AA	100	300	1.3 [‡]	34	97‡	100	300

Notes:

† I_{D} (continuous) is limited by max rated T_{i} .

Mounted on FR4 board, 25mm x 25mm x 1.57mm.

Electrical Characteristics (T₄ = 25°C unless otherwise specified)

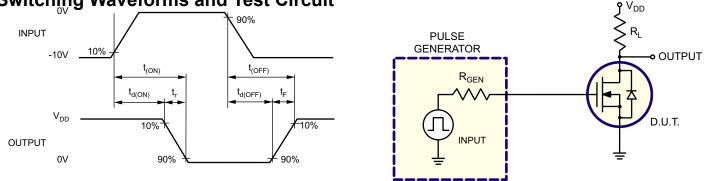
Sym	Parameter	Min	Тур	Мах	Units	Conditions		
BV _{DSX}	Drain-to-source breakdown voltage	450	-	-	V	V _{GS} = -5.0V, I _D = 100µA		
V _{GS(OFF)}	Gate-to-source off voltage	-1.5	-	-3.5	V	V _{DS} = 15V, I _D = 10µA		
$\Delta V_{GS(OFF)}$	Change in $V_{\mbox{\scriptsize GS}(\mbox{\scriptsize OFF})}$ with temperature	-	-	-4.5	mV/ºC	V _{DS} = 15V, Ι _D = 10μΑ		
I _{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
		-	-	1.0	μA	V_{DS} = Max rating, V_{GS} = -5.0V		
I _{D(OFF)}	Drain-to-source leakage current	-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = -5.0V$, $T_{A} = 125^{\circ}C$		
I _{DSS}	Saturated drain-to-source current	120	-	-	mA	V _{GS} = 0V, V _{DS} = 15V		
R _{DS(ON)}	Static drain-to-source on-state resistance	-	-	60	Ω	V _{GS} = 0V, I _D = 100mA		
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.1	%/°C	V _{GS} = 0V, I _D = 100mA		
G _{FS}	Forward transconductance	140	-	-	mmho	V _{DS} = 10V, I _D = 100mA		
C _{ISS}	Input capacitance	-	-	120		V _{GS} = -5.0V,		
C _{oss}	Common source output capacitance	-	-	15	pF	V _{DS} = 25V,		
C _{RSS}	Reverse transfer capacitance	-	-	10		f = 1.0MHz		
t _{d(ON)}	Turn-on delay time	-	-	10				
t,	Rise time	-	-	15		$V_{DD} = 25V,$ $I_{D} = 100 \text{mA},$ $R_{GEN} = 25\Omega,$		
t _{d(OFF)}	Turn-off delay time	-	-	20	ns			
t _r	Fall time	-	-	35		GEN '		
V _{SD}	Diode forward voltage drop	-	-	1.8	V	V _{GS} = -5.0V, I _{SD} = 100mA		
t _{rr}	Reverse recovery time	-	800	-	ns	V _{GS} = -5.0V, I _{SD} = 100mA		

Notes:

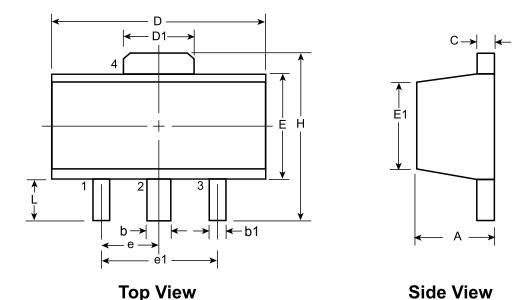
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit



3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbol		Α	b	b1	С	D	D1	Е	E1	е	e1	н	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.13	1.50 BSC	3.00 BSC	3.94	0.89
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version D070908.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>http://www.supertex.com/packaging.html</u>.)

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